NCE P-Channel Enhancement Mode Power MOSFET

Description

The NCE60P16AQ uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or power management.

Application

- Power management
- Load switch

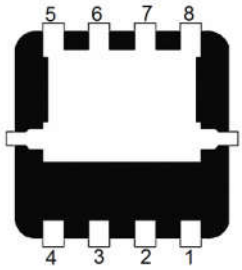
100% UIS TESTED!
100% ΔVds TESTED!

General Features

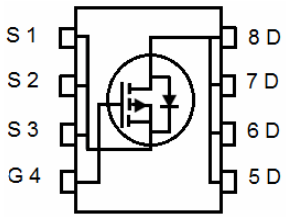
- V_{DS} = -60V,I_D = -16A
  $R_{DS(ON)}$ <65mΩ @ V_{GS}=-10V
  $R_{DS(ON)}$ <85mΩ @ V_{GS}=-4.5V
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

DFN 3.3X3.3

Top View



Bottom View



Schematic Diagram

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCE60P16AQ	NCE60P16AQ	DFN3.3X3.3-8L	-	-	-

Absolute Maximum Ratings (T_C=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	-60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	-16	A
Pulsed Drain Current	I_{DM}	-64	A
Maximum Power Dissipation	P_D	30	W
Operating Junction and Storage Temperature Range	T_J,T_{STG}	-55 To 150	℃

Thermal Characteristic

Thermal Resistance, Junction-to-Case(Note 2)	$R_{\theta JA}$	4.2	℃/W

Electrical Characteristics (T_C=25℃unless otherwise noted)

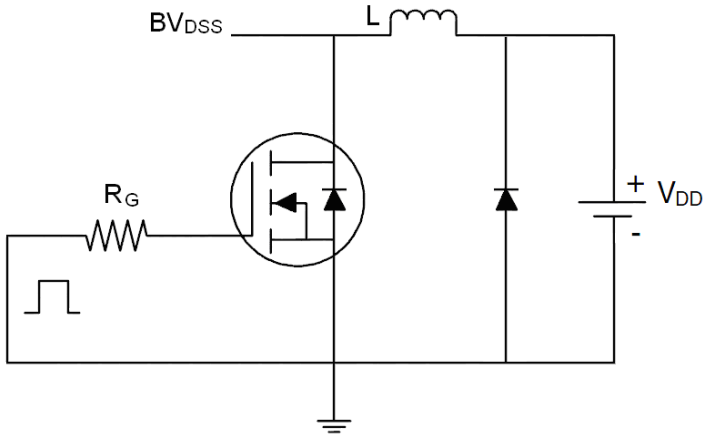
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V I_D=-250μA	-60	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=-60V,V_{GS}=0V	-	-	-1	μA
Gate-Body Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=-250μA	-1.0	-1.5	-2.0	V
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS}=-10V, I_D=-8A	-	55	65	mΩ
		V_{GS}=-4.5V, I_D=-8A	-	70	85	mΩ
Forward Transconductance	g_{FS}	V_{DS}=-5V,I_D=-8A	-	10	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	C_{lss}	V_{DS}=-30V,V_{GS}=0V, F=1.0MHz	-	1153	-	PF
Output Capacitance	C_{oss}		-	93.7	-	PF
Reverse Transfer Capacitance	C_{rss}		-	77.7	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	$t_{d(on)}$	V_{DD}=-30V, R_L=6Ω, V_{GS}=-10V,R_G=3Ω	-	8	-	nS
Turn-on Rise Time	t_r		-	5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	32	-	nS
Turn-Off Fall Time	t_f		-	8	-	nS
Total Gate Charge	Q_g	V_{DS}=-30,I_D=-8A, V_{GS}=-10V	-	15.8	-	nC
Gate-Source Charge	Q_{gs}		-	2.7	-	nC
Gate-Drain Charge	Q_{gd}		-	3.5	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V_{SD}	V_{GS}=0V,I_S=-8A	-		-1.2	V
Diode Forward Current (Note 2)	I_S		-	-	-16	A
Reverse Recovery Time	t_{rr}	T_J = 25°C, I_F =- 8A di/dt = -100A/μs(Note3)	-	27		nS
Reverse Recovery Charge	Qrr		-	32		nC

Notes:

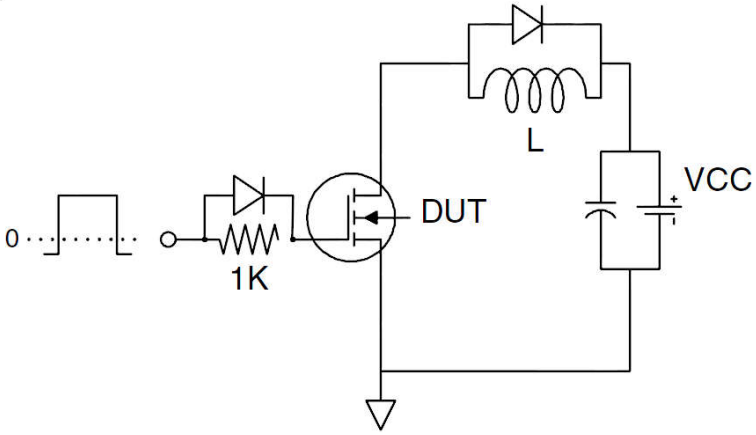
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production

Test Circuit

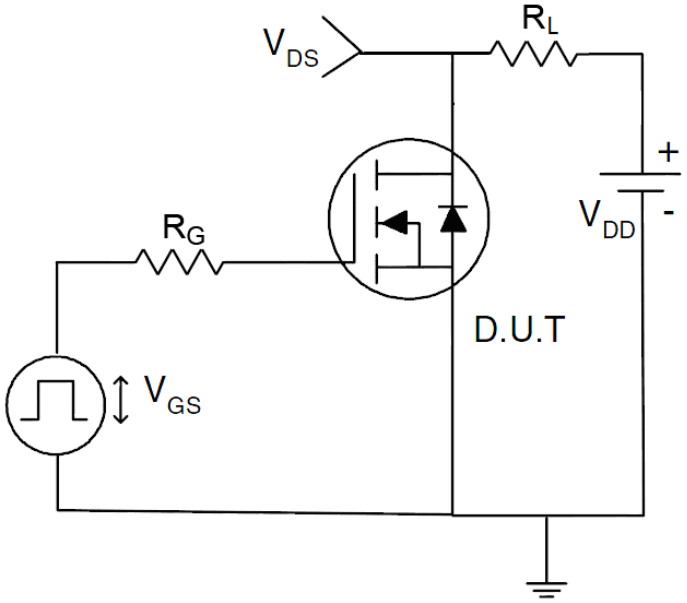
1）E_{AS} test Circuit



2）Gate charge test Circuit



3）Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

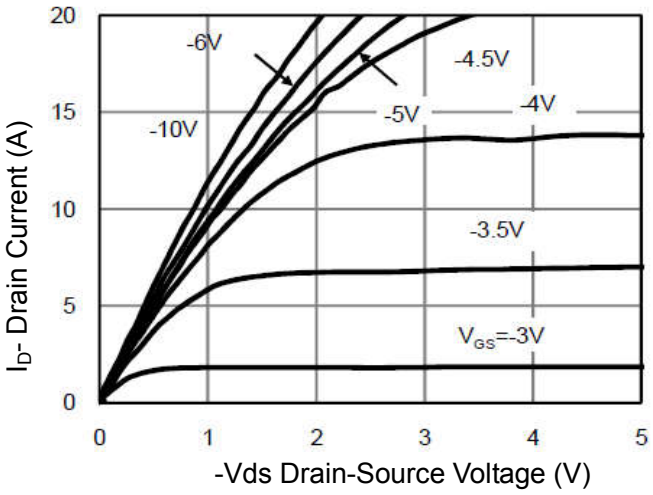


Figure 1 Output Characteristics

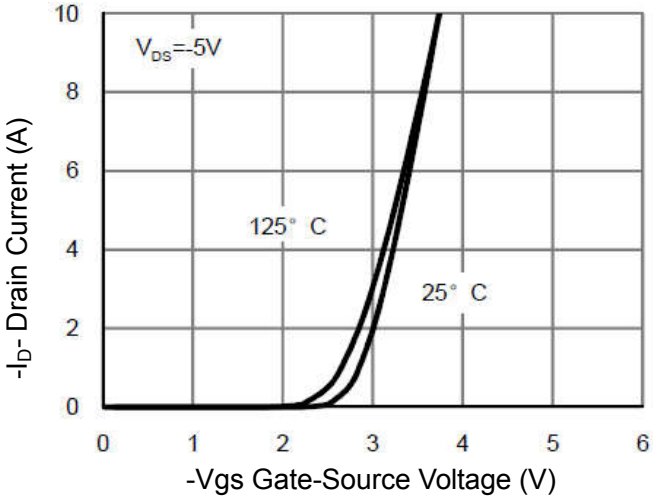


Figure 2 Transfer Characteristics

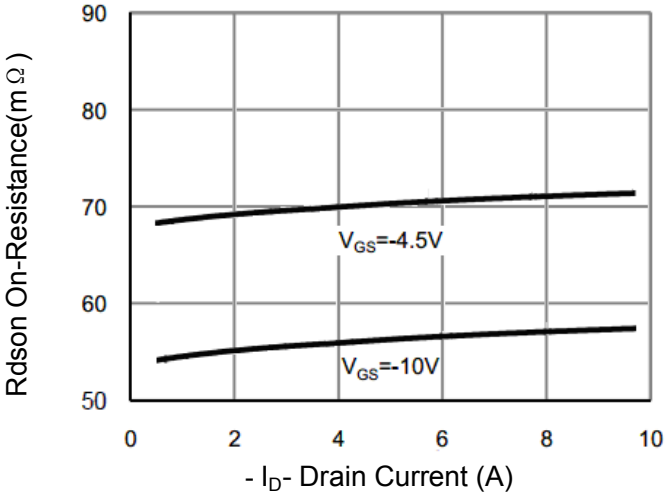


Figure 3 Rdson- Drain Current

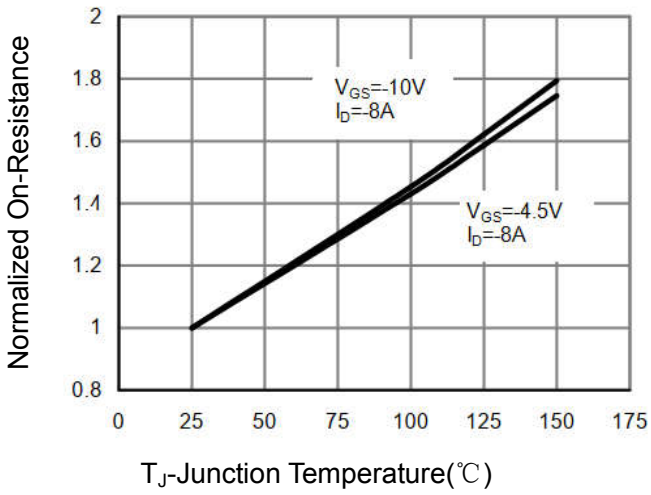


Figure 4 Rdson-Junction Temperature

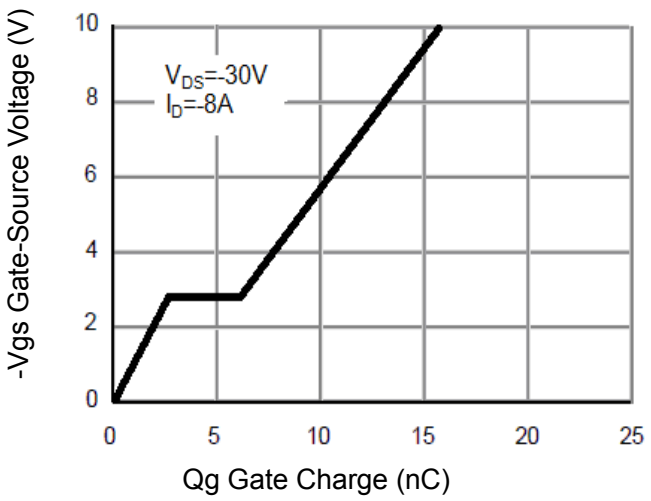


Figure 5 Gate Charge

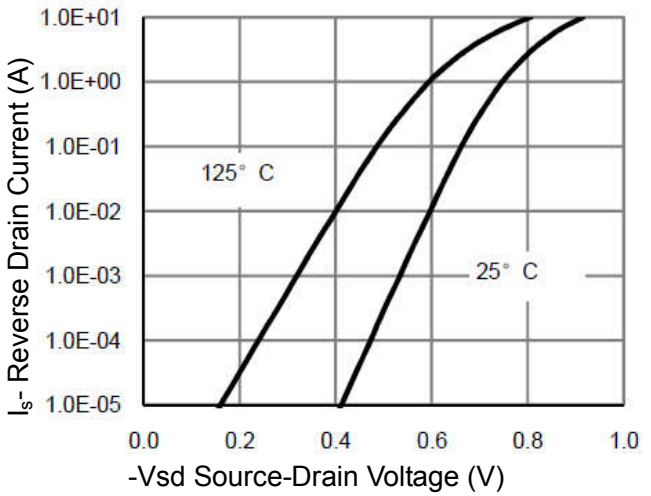


Figure 6 Source- Drain Diode Forward

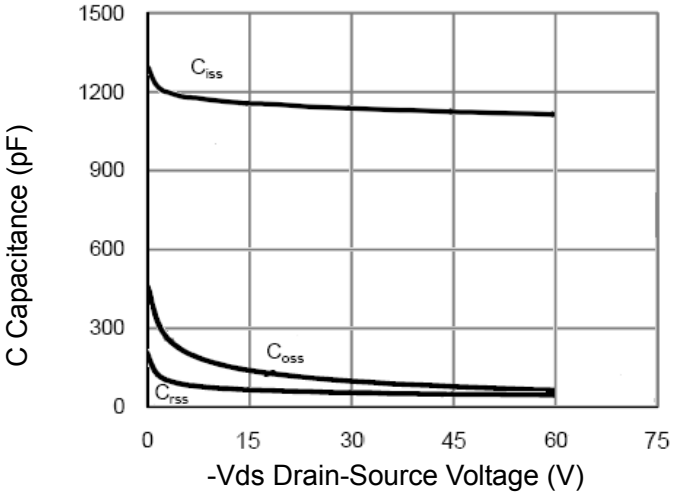


Figure 7 Capacitance vs Vds

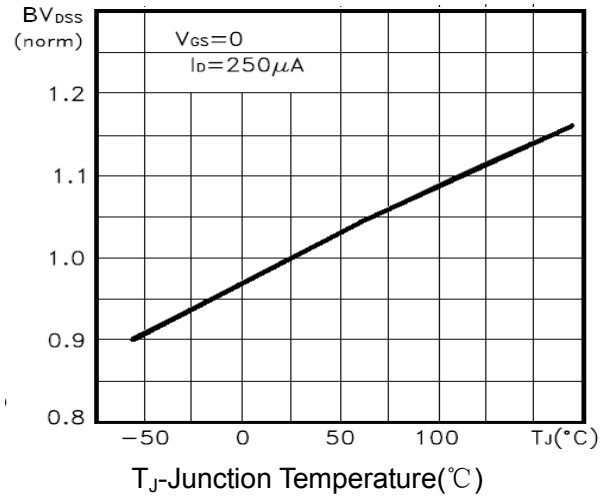


Figure 9 BV_{DSS} vs Junction Temperature

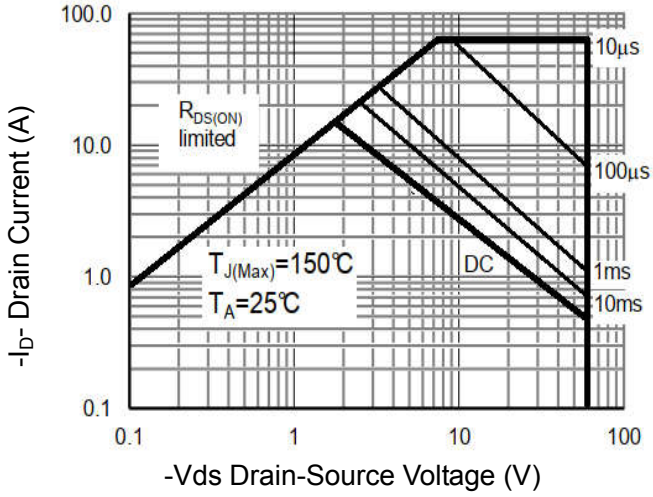


Figure 8 Safe Operation Area

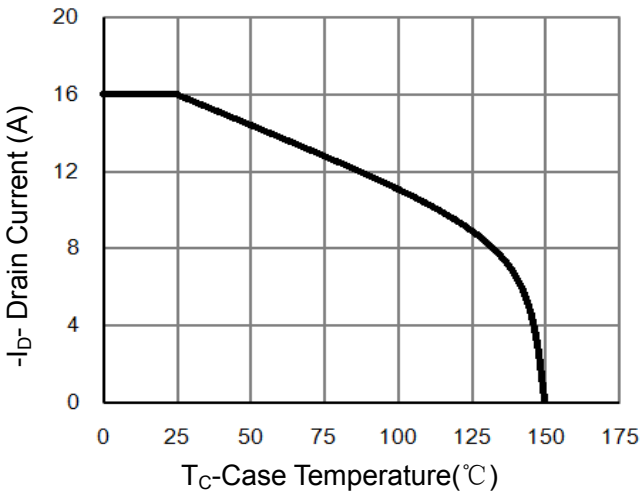


Figure 10 ID Current De-rating

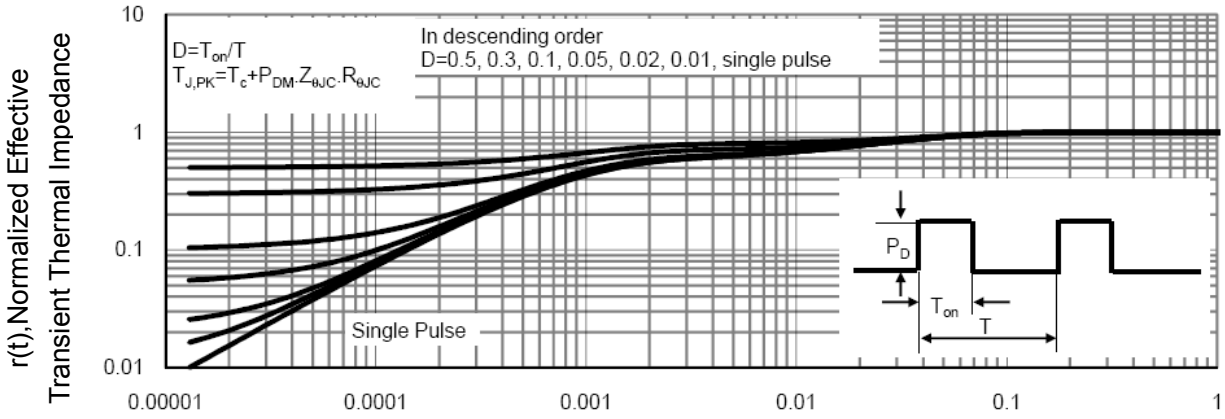
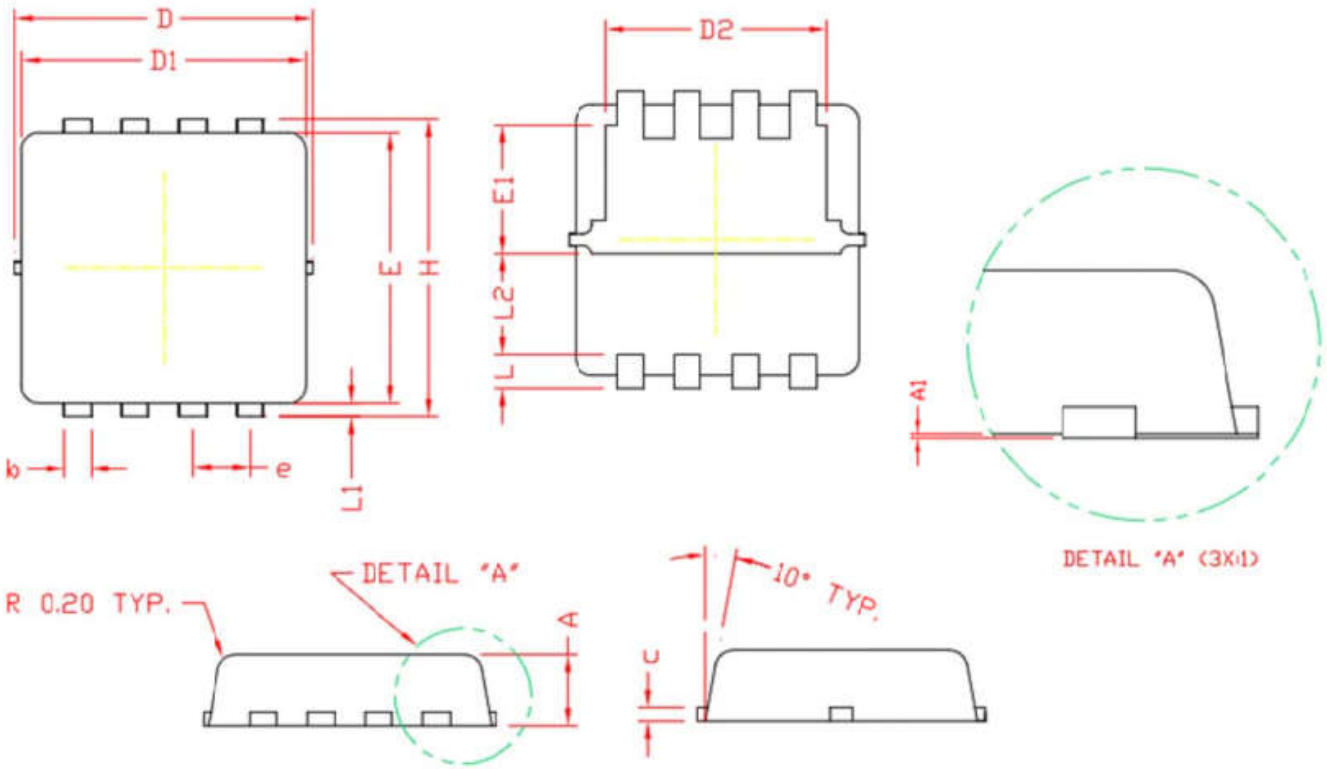


Figure 11 Normalized Maximum Transient Thermal Impedance

DFN3.3X3.3-8L Package Information



COMMON DIMENSIONS

(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	0.70	0.80	0.90
A1	0.00	0.03	0.05
b	0.24	0.30	0.35
c	0.10	0.15	0.20
D	3.25	3.32	3.40
D1	3.05	3.15	3.25
D2	2.40	2.50	2.60
E	3.00	3.10	3.20
E1	1.35	1.45	1.55
e	0.65 BSC.		
H	3.20	3.30	3.40
L	0.30	0.40	0.50
L1	0.10	0.15	0.20
L2	1.13 REF.		

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